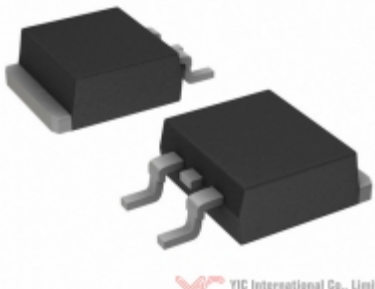










	<h2 style="color: red;">FQB25N33TM</h2>
	<p>Hersteller-Teilenummer: FQB25N33TM</p> <hr/> <p>Hersteller / Marke: AMI Semiconductor / ON Semiconductor</p> <hr/> <p>Teil der Beschreibung: MOSFET N-CH 330V 25A D2PAK</p> <hr/> <p>Datenblätter:  FQB25N33TM.pdf</p> <hr/> <p>RoHs Status: Bleifrei / RoHS-konform</p> <hr/> <p>Lagerzustand: New original, 21999 pcs Stock Available.</p> <hr/> <p>Liefern von: Hong Kong</p> <hr/> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	FQB25N33TM
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	MOSFET N-CH 330V 25A D2PAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	21999 pcs Stock
detaillierte Beschreibung	N-Channel 330V 25A (Tc) 3.1W (Ta), 250W (Tc)
Serie	QFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-263-3, D ² Pak (2 Leads + Tab), TO-263AB
Supplier Device-Gehäuse	D ² PAK (TO-263AB)
Verlustleistung (max)	3.1W (Ta), 250W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	330V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	25A (Tc)
Rds On (Max) @ Id, Vgs	230 mOhm @ 12.5A, 10V
VGS (th) (Max) @ Id	5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	75nC @ 15V
Eingabekapazität (Ciss) (Max) @ Vds	2010pF @ 25V
Antriebsspannung (Max Rds On, Min Rds On)	10V
Vgs (Max)	±30V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	FQB25N33TMTR

FQB25N33TM ist neu im Original, Suche FQB25N33TM Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie FQB25N33TM AMI Semiconductor / ON Semiconductor mit Garantie und Vertrauen. Anfrage FQB25N33TM: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>FQB25N33TM_F085 Fairchild/ON Semiconductor FQB25N33TM_F085 Fairchild/ON Semiconductor</p>	 <p>FQB25N33TM-F085 AMI Semiconductor / ON Semiconductor MOSFET N-CH 330V 25A D2PAK</p>	 <p>FQB22P10TM_F085 Fairchild/ON Semiconductor FQB22P10TM_F085 Fairchild/ON Semiconductor</p>	 <p>FQB25N33 FAIRCHI FQB25N33 FAIRCHI</p>
 <p>FQB25N33TM Fairchild/ON Semiconductor MOSFET N-CH 330V 25A D2PAK</p>	 <p>FQB24N08TM Fairchild/ON Semiconductor MOSFET N-CH 80V 24A D2PAK</p>	 <p>FQB24N08TM AMI Semiconductor / ON Semiconductor MOSFET N-CH 80V 24A D2PAK</p>	 <p>FQB27N25 FAIRCHI FQB27N25 FAIRCHI</p>

heiße Teile

Mehr

⊗ FQB19N10LTM	↔ FQB19N10LTM	⇒ FQB19N10TM	D FQB19N10TM	↗ FQB19N20
⊕ FQB19N20C	⊗ FQB19N20CTM	D FQB19N20CTM	⇒ FQB19N20L	↗ FQB19N20LTM
⊗ FQB19N20LTM	⊕ FQB19N20TM	⊗ FQB19N20TM	↔ FQB1N60TM	↗ FQB1N60TM
D FQB20N06L	⊗ FQB20N60FTM	⊕ FQB20N60TM	⊗ FQB22P10	↗ FQB22P10TM
⇒ FQB22P10TM	↔ FQB22P10TM_F085	⊗ FQB24N08TM	⊕ FQB24N08TM	↗ FQB25N33
↔ FQB25N33TM	⇒ FQB25N33TM_F085	D FQB27N25TM	⊗ FQB27P06	⊕ FQB27P06TM
⊗ FQB27P06TM	D FQB2N50C	⇒ FQB2N60TM	↔ FQB2N60TM	↗ FQB2N80TM
⊕ FQB2N80TM	⊗ FQB2NA90TM	↔ FQB2NA90TM	⇒ FQB2P25TM	↗ FQB2P25TM
⊗ FQB30N06	⊕ FQB30N06L	⊗ FQB30N06LTM	D FQB30N06LTM	↗ FQB30N06TM
↔ FQB30N06TM	⊗ FQB32N12V2	⊕ FQB32N12V2TM	⊗ FQB32N12V2TM	↗ FQB32N20

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

Copyright © 2019 YIC International Co., Limited